

## THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND  
CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

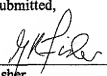
*Customer Number: 76681*

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

*Customer Number: 76681*

Respectfully submitted,

Date: 5/13/2008

  
\_\_\_\_\_  
Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)


**MEMC Electronic Materials, Inc.**, a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in *U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.*

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to **MEMC Electronic Materials, Inc.** via Assignment(s) recorded with the United States Patent and Trademark Office at the *Reel/Frame Numbers on the attached Schedule A.*

The undersigned, **Dr. Graham Fisher, Director of Intellectual Property**, has full authorization to act on behalf of Assignee **MEMC Electronic Materials, Inc.**

Respectfully submitted,

Date: 5/13/2008

  
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Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

**APPENDIX A**  
**Owned by MEMC Electronic Materials, Inc.**

ATTORNEY REFERENCE	CONF. NO	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
MEMC2463.2	1288	US-2003-011604-A1 6/26/2003	10/26/2003 9/30/2002	6,652,846 1/25/2003	MEMC Electronic Materials, Inc.	Continuation of 09/833,232 which is a continuation of 09/344,038 recorded at 01/0461/0004	PROCESS FOR GROWING A SILICON CRYSTAL SEGMENT SUBSTANTIALLY FREE FROM AGGLOMERATED INTRINSIC POINT DEFECTS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS
MEMC2462.1	7225	US-2002-003953-A1 7/14/2002	10/22/1997 12/13/2001	7,009,874 3/7/2006	MEMC Electronic Materials, Inc.	01/2728/0205	PROCESS FOR RECLAIMING SEMICONDUCTOR WAFERS AND RECLAIMED WAFERS
MEMC2464	5164	US-2002-0004305-A1 1/10/2002	09/481,080 1/11/2002	6,376,395 4/23/2002	MEMC Electronic Materials, Inc.	01/0697/0209	SEMICONDUCTOR WAFER MANUFACTURING PROCESS
MEMC2466.1	6579		09/481,194 10/19/2000	6,503,822 1/7/2003	MEMC Electronic Materials, Inc.	Division of 09/039,826 recorded at 01/013207/16	ELECTRICAL RESISTANCE HEATER AND METHOD FOR CRYSTAL GROWING APPARATUS
MEMC2471	9391	US-2001-000811-A1 7/16/2001	09/044,709 6/29/1999	6,362,795 12/11/2001	MEMC Electronic Materials, Inc.	01/0189/0956	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS
MEMC2471.1	4680	US-2002-0052480-A1 7/16/2002	10/035,540 10/23/2001	6,662,123 5/13/2003	MEMC Electronic Materials, Inc.	Continuation of 09/0344,709 recorded at 01/0189/0956	PROCESS FOR GROWING DEFECT-FREE SILICON WHEREIN THE GROWN SILICON IS COOLED IN A SEPARATE CHAMBER
MEMC2471.2	3684	US-2004-0006770-A1 1/9/2004	10/437,141 5/13/2003	6,913,647 7/5/2005	MEMC Electronic Materials, Inc.	Continuation of 10/035,540 which is a continuation of 09/0344,709 recorded at 01/0189/0956	PROCESS FOR COOLING A SILICON INGOT HAVING A VACANCY DOMINATED REGION TO PRODUCE DEFECT FREE SILICON
MEMC2477	8073		09/035,616 7/16/1999	6,114,245 9/5/2000	MEMC Electronic Materials, Inc.	Continuation of 09/015,975 recorded at 8681/0787	METHOD OF PROCESSING SEMICONDUCTOR WAFERS
28744-161 (MEMC2489)	3575		09/366,850 8/4/1999	6,828,690 12/7/2004	MEMC Electronic Materials, Inc.	01/0225/0266	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES
MEMC2489.1	1211	US-2005-0006796 A1 1/13/2005	10/611,985 8/5/2004	7,242,037 7/10/2007	MEMC Electronic Materials, Inc.	Division of 09/356,650 recorded at 01/0225/0266	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTION IN HIGH PERFORMANCE SILICON POWER DEVICES
MEMC2493	3777		09/421,167 10/19/1999	6,203,611 3/20/2001	MEMC Electronic Materials, Inc.	01/0344/0075	METHOD OF CONTROLLING GROWTH OF A SEMICONDUCTOR CRYSTAL TO AUTOMATICALLY TRANSITION FROM TAPER GROWTH TO TARGET DIAMETER GROWTH
MEMC2495	1207		09/370,383 8/23/1999	5,336,969 1/9/2002	MEMC Electronic Materials, Inc.	01/0296/0636	NON-OXYGEN PRECIPITATING CVD/HRFALSI SILICON WAFERS